

FEATURES

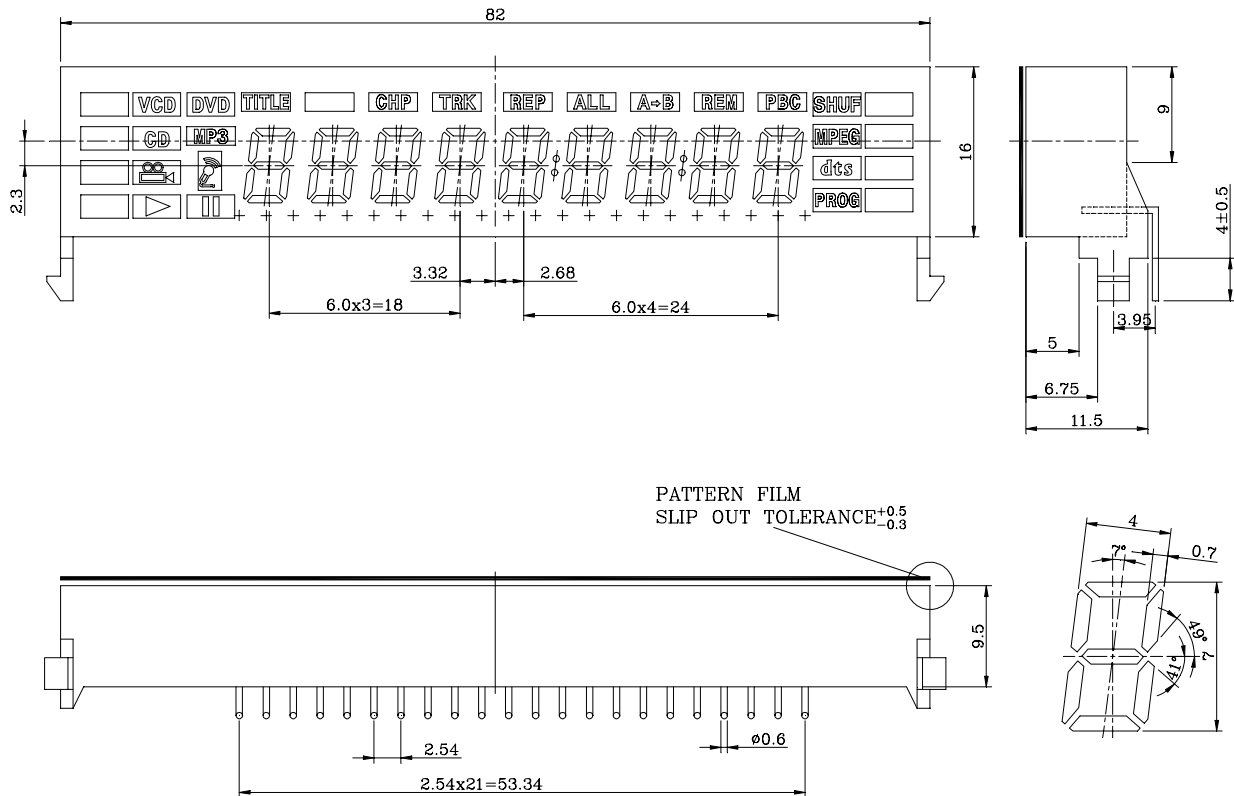
- * 0.27 INCH (7.0 mm) DIGIT HEIGHT.
- * CONTINUOUS UNIFORM SEGMENTS.
- * LOW POWER REQUIREMENT.
- * EXCELLENT CHARACTERS APPEARANCE.
- * HIGH BRIGHTNESS & HIGH CONTRAST.
- * WIDE VIEWING ANGLE.
- * SOLID STATE RELIABILITY.

DESCRIPTION

The LTG-Y2K31M is a 0.27 inch (7.0 mm) digit height seven-segment display. The device is multi-color applicable display. The green LED chips, which are made from GaP on a transparent GaP substrate. The red orange & amber LED chips, which are made from GaAsP on a transparent GaP.

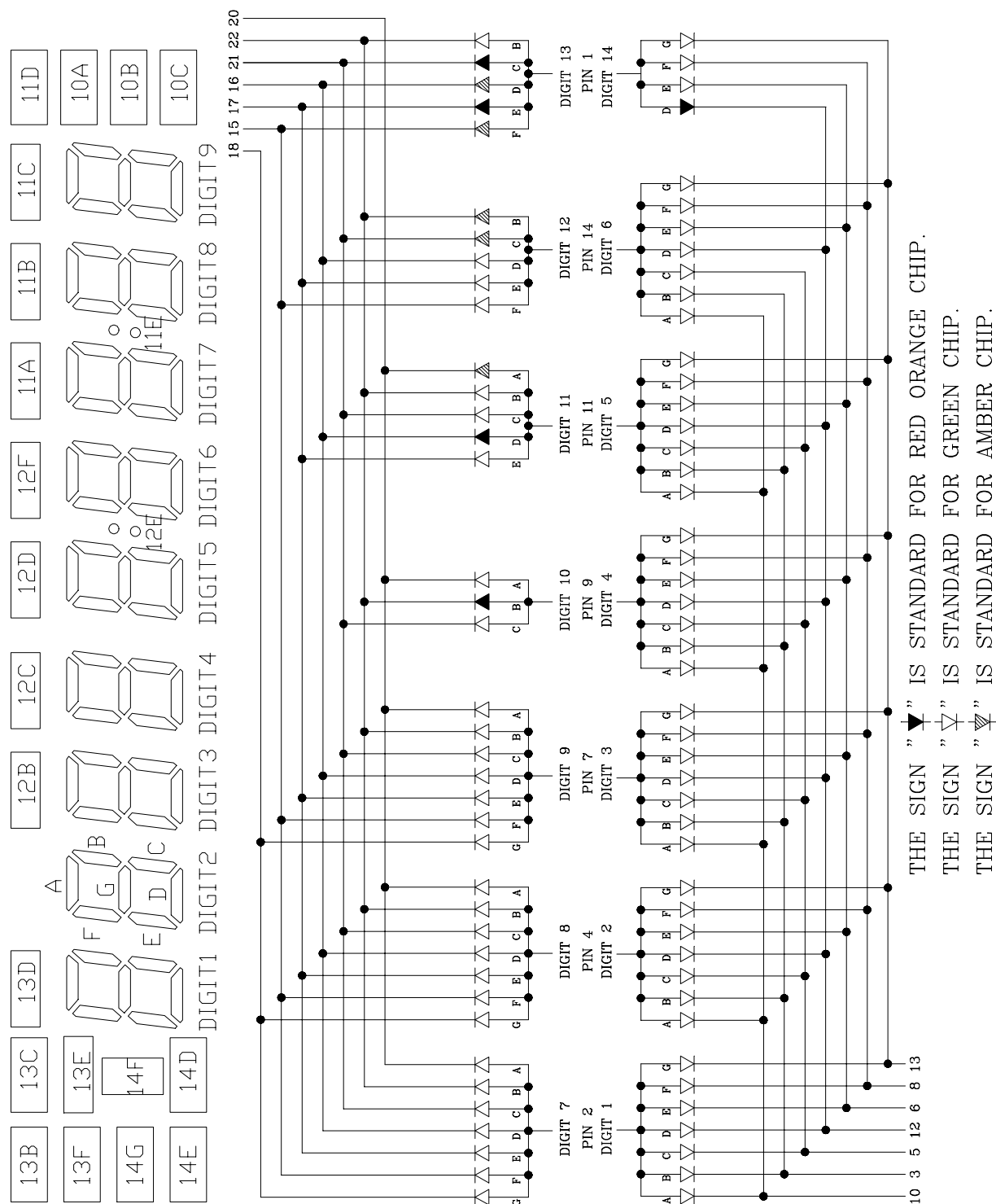
DEVICE

PART NO.	DESCRIPTION
MULTI-COLOR	Multiplex Common Anode
LTG-Y2K31M	

PACKAGE DIMENSIONS


NOTES: All dimensions are in millimeters. Tolerances are ± 0.25 mm unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



THE SIGN "▼" IS STANDARD FOR RED ORANGE CHIP.

THE SIGN " ∇ " IS STANDARD FOR GREEN CHIP.

THE SIGN "Z" IS STANDARD FOR AMBER CHIP.

PIN CONNECTION

No.	CONNECTION
1	COMMON ANODE (DIGIT 13,14)
2	COMMON ANODE (DIGIT 1,7)
3	CATHODE B
4	COMMON ANODE (DIGIT 2,8)
5	CATHODE C
6	CATHODE E
7	COMMON ANODE (DIGIT 3,9)
8	CATHODE F
9	COMMON ANODE (DIGIT 4,10)
10	CATHODE A
11	COMMON ANODE (DIGIT 5,11)
12	CATHODE D
13	CATHODE G
14	COMMON ANODE (DIGIT 6,12)
15	CATHODE F
16	CATHODE D
17	CATHODE E
18	CATHODE G
19	NO CONNECTION
20	CATHODE A
21	CATHODE C
22	CATHODE B

ABSOLUTE MAXIMUM RATING AT T_a=25°C

PARAMETER	GREEN	RED ORANGE	AMBER	UNIT
Power Dissipation Per Chip	75	75	75	mW
Peak Forward Current Per Chip (1/10 Duty Cycle, 0.1ms Pulse Width)	100	100	100	mA
Continuous Forward Current Per Chip	25	25	25	mA
Derating Linear From 25°C Per Chip	0.28	0.28	0.28	mA/°C
Reverse Voltage Per Chip	5	5	5	V
Operating Temperature Range	-35°C to +105°C			
Storage Temperature Range	-35°C to +105°C			
Solder Temperature: max 260°C for max 3sec at 1.6mm below seating plane				

ELECTRICAL / OPTICAL CHARACTERISTICS AT T_a=25°C
DIGIT(GREEN)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity Per Segment	I _v		930		μcd	I _F =10mA
Peak Emission Wavelength	λ _p		565		nm	I _F =20mA
Spectral Line Half-Width	Δλ		30		nm	I _F =20mA
Dominant Wavelength	λ _d		569		nm	I _F =20mA
Forward Voltage Per Chip	V _F		2.1	2.6	V	I _F =20mA
Reverse Current Per Chip	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =10mA

ICON(GREEN)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity Per Segment	I _v		1170		μcd	I _F =10mA
Peak Emission Wavelength	λ _p		565		nm	I _F =20mA
Spectral Line Half-Width	Δλ		30		nm	I _F =20mA
Dominant Wavelength	λ _d		569		nm	I _F =20mA
Forward Voltage Per Chip	V _F		2.1	2.6	V	I _F =20mA
Reverse Current Per Chip	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =10mA

ICON(RED ORANGE)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity Per Segment	I _v		1060		μcd	I _F =10mA
Peak Emission Wavelength	λ _p		630		nm	I _F =20mA
Spectral Line Half-Width	Δλ		40		nm	I _F =20mA
Dominant Wavelength	λ _d		621		nm	I _F =20mA
Forward Voltage Per Chip	V _F		2.0	2.6	V	I _F =20mA
Reverse Current Per Chip	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =10mA

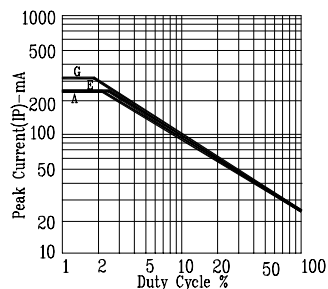
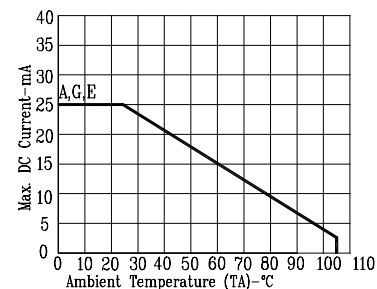
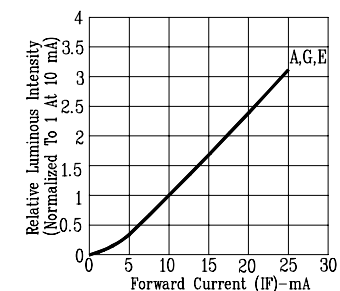
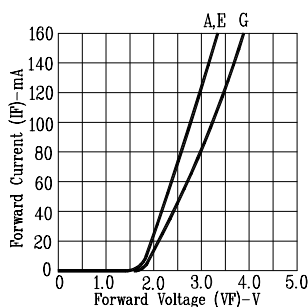
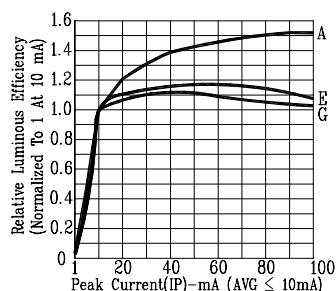
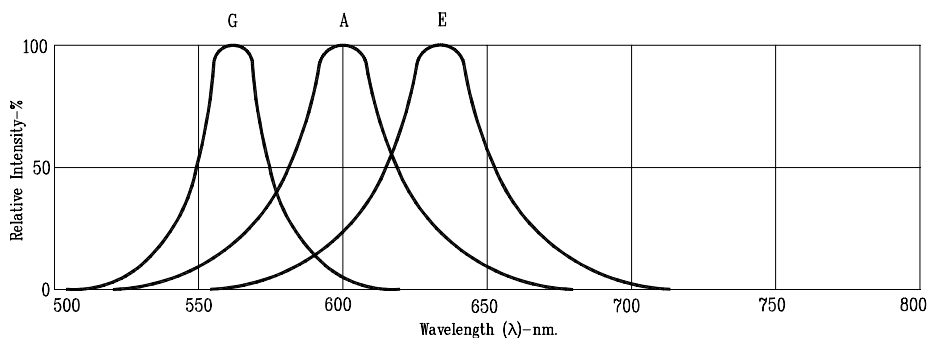
ICON(AMBER)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity Per Segment	I _v		650		μcd	I _F =10mA
Peak Emission Wavelength	λ _p		610		nm	I _F =20mA
Spectral Line Half-Width	Δλ		35		nm	I _F =20mA
Dominant Wavelength	λ _d		602		nm	I _F =20mA
Forward Voltage Per Chip	V _F		2.1	2.6	V	I _F =20mA
Reverse Current Per Chip	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =10mA

Note: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (Commission Internationale De L'Eclairage) eye-response curve.

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

(25°C Ambient Temperature Unless Otherwise Noted)



NOTE: A=AMBER G=GREEN E=RED ORANGE